2SK156

SILICON N-CHANNEL JUNCTION-TYPE FIELD EFFECT TRANSISTOR FOR CONDENSER MICROPHONE IMPEDANCE CONVERSION

ABSOLUTE MAXIMUM RATINGS/T_a = 25°C

			unit
Drain-gate voltage	V_{DGO}	20	V
Gate current	I_G	10	mA
Allowable power dissipation	P_D	100	mW
Junction temperature	T_j	125	°C
Storage ambient temperature	T_{stg}	−40 ~ +125	°C

ELECTRICAL CHARACTERISTICS/T_a = 25°C

			min	typ	max	unit
Drain current	I_{DSS}*	V_{DS} = 10 V	0.06*		1.5*	mA

[T_a = 25°C, V_{CC} = 4.5 V, R_D = 680 Ω, C_{in} = 15 pF, in specified test circuit (conforming with application circuit)]

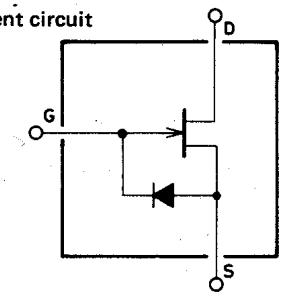
			min	typ	max	unit
Transmission loss voltage-drop characteristics	$\triangle G_{VV}$	Vcc = 4.5 ~ 1.5 V, f = 1 kHz			−3	dB
Transmission loss frequency characteristics	$\triangle G_{vf}$	f = 1 k ~ 110 Hz, V_{in} = 10 mV			−1	dB
Input impedance	z_{in}	f = 1 kHz	20 M			Ω
Output noise voltage	V_{NO}	V_{in} = 0, A-curve			−110	dB

* 2SK156 is graded as follows by drain current I_{DSS}:

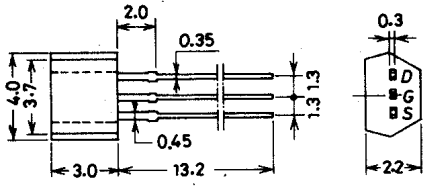
~~0.06 A 0.3 0.25 B 0.8 0.6 C 1.5~~ mA

J	K	L	M
60 - 180	150 - 300	250 - 450	400 - 800

Equivalent circuit



Case Outline 2001
(unit: mm)



SANYO: SP

D: Drain
G: Gate
S: Source

These specifications are subject to change without notice.

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